

IGBT

High speed DuoPack: IGBT in Trench and Fieldstop technology with soft, fast recovery anti-parallel diode

IKP20N60H3

600V high speed switching series third generation

Datasheet

Industrial & Multimarket

High speed IGBT in Trench and Fieldstop technology

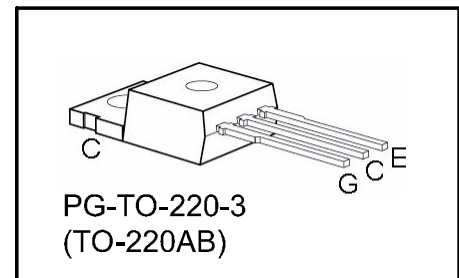
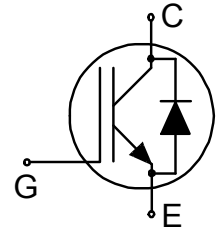
Features:

TRENCHSTOP™ technology offering

- very low V_{CEsat}
- low EMI
- maximum junction temperature 175°C
- qualified according to JEDEC for target applications
- Pb-free lead plating; RoHS compliant
- complete product spectrum and PSpice Models:
<http://www.infineon.com/igbt/>

Applications:

- uninterruptible power supplies
- welding converters
- converters with high switching frequency



Key Performance and Package Parameters

| Type | V_{CE} | I_C | $V_{CEsat}, T_{vj}=25^\circ\text{C}$ | T_{vjmax} | Marking | Package |
|------------|----------|-------|--------------------------------------|-------------|---------|------------|
| IKP20N60H3 | 600V | 20A | 1.95V | 175°C | K20H603 | PG-TO220-3 |



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Maximum ratings

| Parameter | Symbol | Value | Unit |
|---|-------------|---------------|------------------|
| Collector-emitter voltage | V_{CE} | 600 | V |
| DC collector current, limited by T_{vjmax} $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$ | I_C | 40.0 20.0 | A |
| Pulsed collector current, t_p limited by T_{vjmax} | I_{Cpuls} | 80.0 | A |
| Turn off safe operating area $V_{CE} \leq 600\text{V}$, $T_{vj} \leq 175^\circ\text{C}$ | - | 80.0 | A |
| Diode forward current, limited by T_{vjmax} $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$ | I_F | 20.0 10.0 | A |
| Diode pulsed current, t_p limited by T_{vjmax} | I_{Fpuls} | 80.0 | A |
| Gate-emitter voltage | V_{GE} | ± 20 | V |
| Short circuit withstand time $V_{GE} = 15.0\text{V}$, $V_{CC} \leq 400\text{V}$ Allowed number of short circuits < 1000 Time between short circuits: $\geq 1.0\text{s}$ $T_{vj} = 150^\circ\text{C}$ | t_{SC} | 5 | μs |
| Power dissipation $T_C = 25^\circ\text{C}$ Power dissipation $T_C = 100^\circ\text{C}$ | P_{tot} | 170.0 85.0 | W |
| Operating junction temperature | T_{vj} | -40...+175 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55...+150 | $^\circ\text{C}$ |
| Soldering temperature, wave soldering 1.6 mm (0.063 in.) from case for 10s | | 260 | $^\circ\text{C}$ |
| Mounting torque, M3 screw Maximum of mounting processes: 3 | M | 0.6 | Nm |

Thermal Resistance

| Parameter | Symbol | Conditions | Max. Value | Unit |
|--|---------------|------------|------------|------|
| Characteristic | | | | |
| IGBT thermal resistance, junction - case | $R_{th(j-c)}$ | | 0.88 | K/W |
| Diode thermal resistance, junction - case | $R_{th(j-c)}$ | | 1.89 | K/W |
| Thermal resistance junction - ambient | $R_{th(j-a)}$ | | 62 | K/W |

Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | | | Unit |
|--------------------------------------|---------------|--|-------------|----------------------|----------------|---------------|
| | | | min. | typ. | max. | |
| Static Characteristic | | | | | | |
| Collector-emitter breakdown voltage | $V_{(BR)CES}$ | $V_{GE} = 0\text{V}, I_C = 2.00\text{mA}$ | 600 | - | - | V |
| Collector-emitter saturation voltage | V_{CEsat} | $V_{GE} = 15.0\text{V}, I_C = 20.0\text{A}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$ | - - - | 1.95 2.30 2.50 | - - - | V |
| Diode forward voltage | V_F | $V_{GE} = 0\text{V}, I_F = 10.0\text{A}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$ | - - - | 1.65 1.67 1.65 | 2.05 - - | V |
| Gate-emitter threshold voltage | $V_{GE(th)}$ | $I_C = 0.29\text{mA}, V_{CE} = V_{GE}$ | 4.1 | 5.1 | 5.7 | V |
| Zero gate voltage collector current | I_{CES} | $V_{CE} = 600\text{V}, V_{GE} = 0\text{V}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$ | - - | - - | 40.0 1000.0 | μA |
| Gate-emitter leakage current | I_{GES} | $V_{CE} = 0\text{V}, V_{GE} = 20\text{V}$ | - | - | 100 | nA |
| Transconductance | g_{fs} | $V_{CE} = 20\text{V}, I_C = 20.0\text{A}$ | - | 10.9 | - | S |

Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | | | Unit |
|--|-------------|---|-------|-------|------|------|
| | | | min. | typ. | max. | |
| Dynamic Characteristic | | | | | | |
| Input capacitance | C_{ies} | $V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$ | - | 1100 | - | pF |
| Output capacitance | C_{oes} | | - | 70 | - | |
| Reverse transfer capacitance | C_{res} | | - | 32 | - | |
| Gate charge | Q_G | $V_{CC} = 480\text{V}, I_C = 20.0\text{A},$ $V_{GE} = 15\text{V}$ | - | 120.0 | - | nC |
| Internal emitter inductance measured 5mm (0.197 in.) from case | L_E | | - | 7.0 | - | nH |
| Short circuit collector current Max. 1000 short circuits Time between short circuits: $\geq 1.0\text{s}$ | $I_{C(SC)}$ | $V_{GE} = 15.0\text{V}, V_{CC} \leq 400\text{V},$ $t_{SC} \leq 5\mu\text{s}$ $T_{vj} = 150^{\circ}\text{C}$ | - | 120 | - | A |

Switching Characteristic, Inductive Load, at $T_{vj} = 25^{\circ}\text{C}$

| Parameter | Symbol | Conditions | Value | | | Unit |
|----------------------------|--------------|---|-------|------|------|------|
| | | | min. | typ. | max. | |
| IGBT Characteristic | | | | | | |
| Turn-on delay time | $t_{d(on)}$ | $T_{vj} = 25^{\circ}\text{C},$ $V_{CC} = 400\text{V}, I_C = 20.0\text{A},$ $V_{GE} = 0.0/15.0\text{V},$ $r_G = 14.6\Omega, L_{\sigma} = 75\text{nH},$ $C_{\sigma} = 30\text{pF}$ L_{σ}, C_{σ} from Fig. E Energy losses include "tail" and diode reverse recovery. | - | 16 | - | ns |
| Rise time | t_r | | - | 20 | - | ns |
| Turn-off delay time | $t_{d(off)}$ | | - | 194 | - | ns |
| Fall time | t_f | | - | 11 | - | ns |
| Turn-on energy | E_{on} | | - | 0.45 | - | mJ |
| Turn-off energy | E_{off} | - | 0.24 | - | mJ | |
| Total switching energy | E_{ts} | - | 0.69 | - | mJ | |

| | | | | | | |
|--|--------------|--|---|------|---|------------------------|
| Diode reverse recovery time | t_{rr} | $T_{vj} = 25^{\circ}\text{C}$, $V_R = 400\text{V}$, $I_F = 10.0\text{A}$, $di_F/dt = 1000\text{A}/\mu\text{s}$ | - | 112 | - | ns |
| Diode reverse recovery charge | Q_{rr} | | - | 0.39 | - | μC |
| Diode peak reverse recovery current | I_{rrm} | | - | 11.0 | - | A |
| Diode peak rate of fall of reverse recovery current during t_b | di_{rr}/dt | | - | -750 | - | $\text{A}/\mu\text{s}$ |

Switching Characteristic, Inductive Load, at $T_{vj} = 175^{\circ}\text{C}$

| Parameter | Symbol | Conditions | Value | | | Unit |
|-----------|--------|------------|-------|------|------|------|
| | | | min. | typ. | max. | |

IGBT Characteristic

| | | | | | | |
|------------------------|--------------|--|---|------|---|----|
| Turn-on delay time | $t_{d(on)}$ | $T_{vj} = 175^{\circ}\text{C}$, $V_{CC} = 400\text{V}$, $I_C = 20.0\text{A}$, $V_{GE} = 0.0/15.0\text{V}$, $r_G = 14.6\Omega$, $L_{\sigma} = 75\text{nH}$, $C_{\sigma} = 30\text{pF}$ L_{σ} , C_{σ} from Fig. E Energy losses include "tail" and diode reverse recovery. | - | 16 | - | ns |
| Rise time | t_r | | - | 15 | - | ns |
| Turn-off delay time | $t_{d(off)}$ | | - | 227 | - | ns |
| Fall time | t_f | | - | 14 | - | ns |
| Turn-on energy | E_{on} | | - | 0.60 | - | mJ |
| Turn-off energy | E_{off} | | - | 0.36 | - | mJ |
| Total switching energy | E_{ts} | | - | 0.96 | - | mJ |

| | | | | | | |
|--|--------------|---|---|------|---|------------------------|
| Diode reverse recovery time | t_{rr} | $T_{vj} = 175^{\circ}\text{C}$, $V_R = 400\text{V}$, $I_F = 10.0\text{A}$, $di_F/dt = 1000\text{A}/\mu\text{s}$ | - | 191 | - | ns |
| Diode reverse recovery charge | Q_{rr} | | - | 0.91 | - | μC |
| Diode peak reverse recovery current | I_{rrm} | | - | 14.2 | - | A |
| Diode peak rate of fall of reverse recovery current during t_b | di_{rr}/dt | | - | -500 | - | $\text{A}/\mu\text{s}$ |

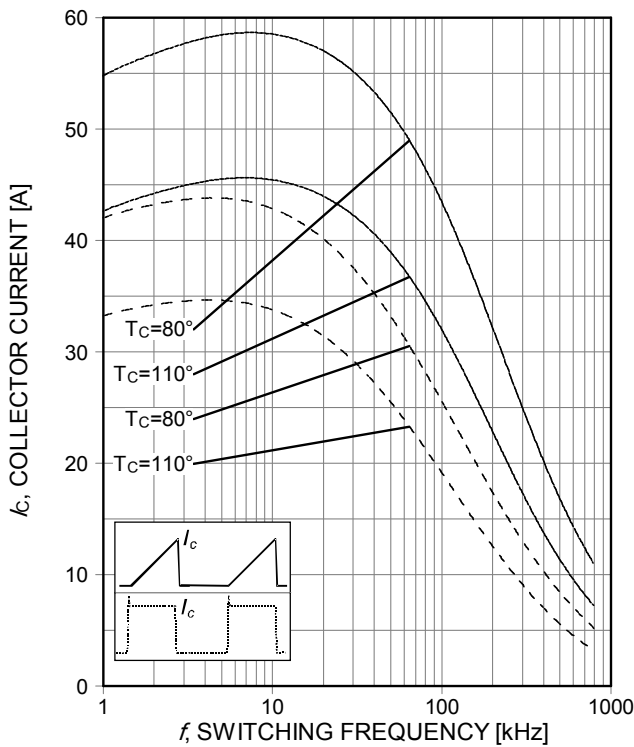


Figure 1. Collector current as a function of switching frequency
 ($T_j \leq 175^\circ\text{C}$, $D=0.5$, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $R_G=14,6\Omega$)

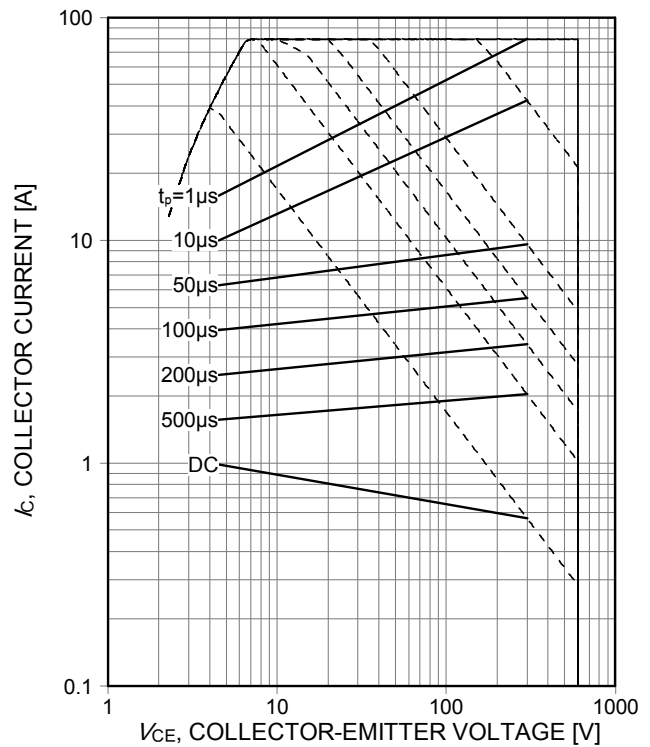


Figure 2. Forward bias safe operating area
 ($D=0$, $T_C=25^\circ\text{C}$, $T_j \leq 175^\circ\text{C}$; $V_{GE}=15\text{V}$)

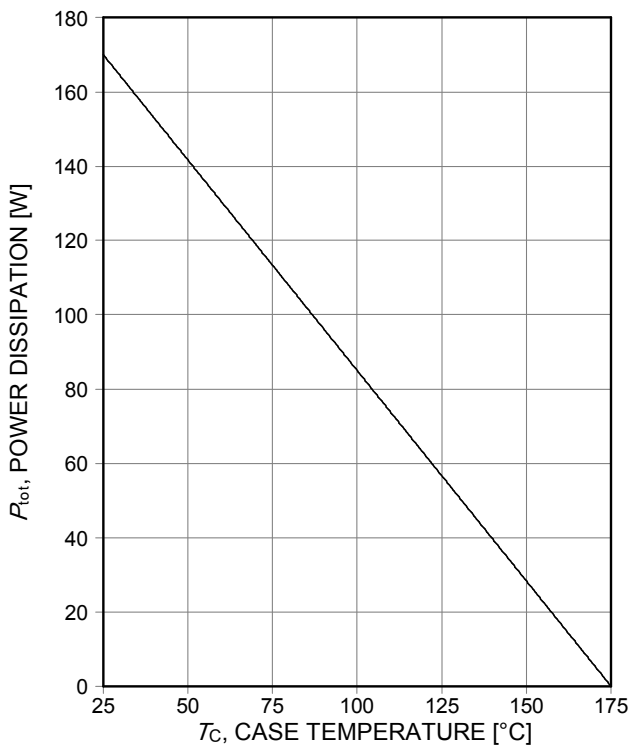


Figure 3. Power dissipation as a function of case temperature
 ($T_j \leq 175^\circ\text{C}$)

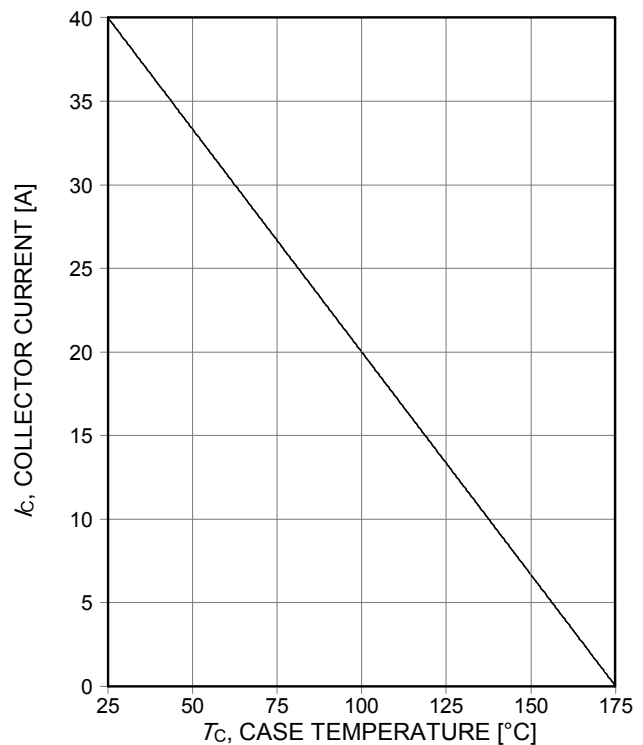


Figure 4. Collector current as a function of case temperature
 ($V_{GE} \geq 15\text{V}$, $T_j \leq 175^\circ\text{C}$)

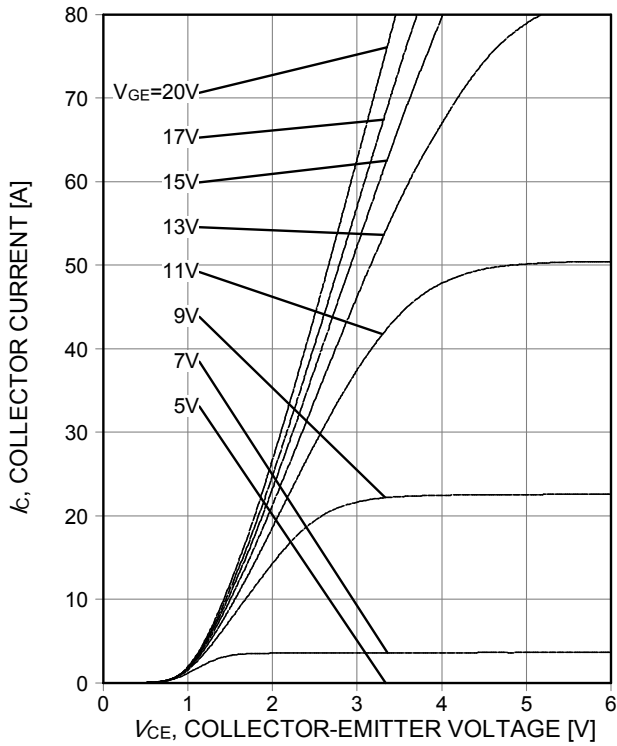


Figure 5. Typical output characteristic
($T_j=25^\circ\text{C}$)

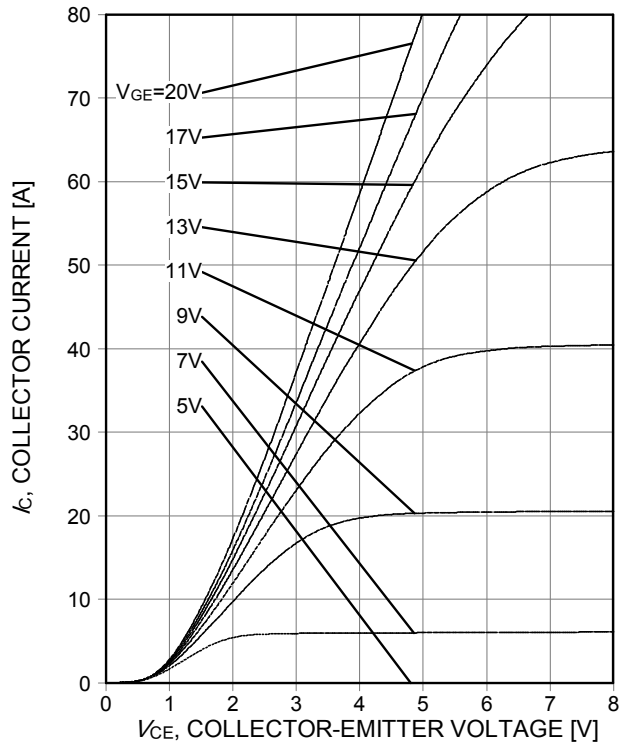


Figure 6. Typical output characteristic
($T_j=175^\circ\text{C}$)

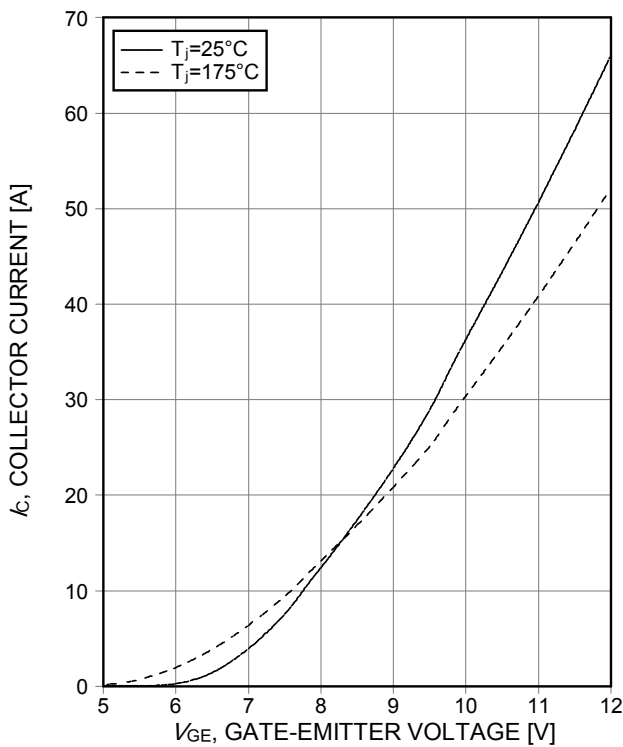


Figure 7. Typical transfer characteristic
($V_{CE}=20\text{V}$)

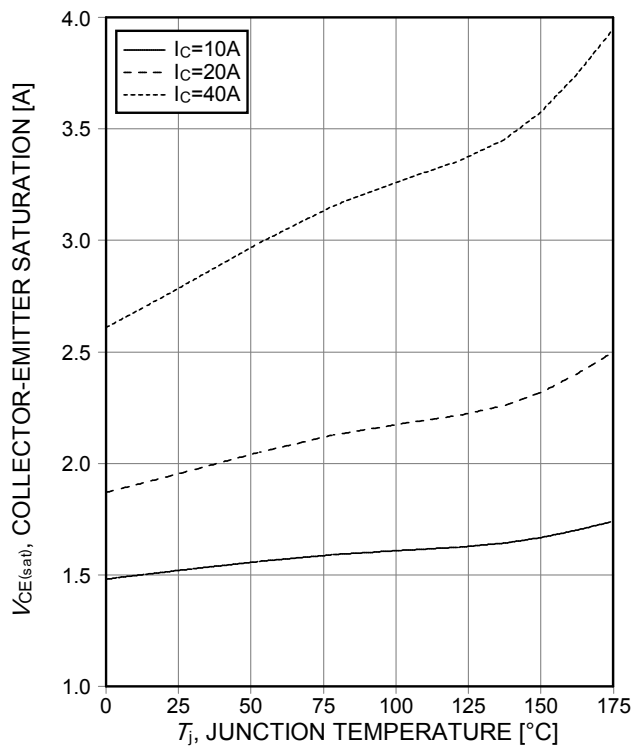


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
($V_{GE}=15\text{V}$)

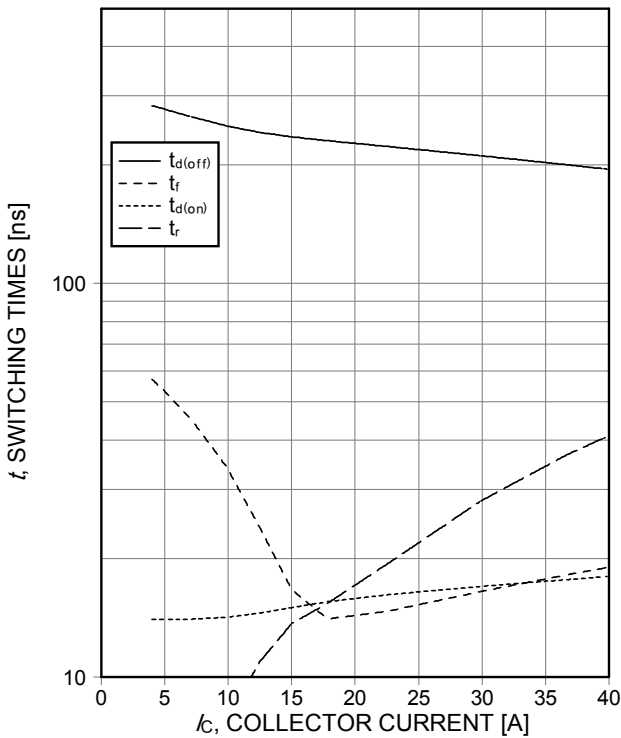


Figure 9. Typical switching times as a function of collector current
 (ind. load, $T_j=175^\circ\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $R_G=14,6\Omega$, test circuit in Fig. E)

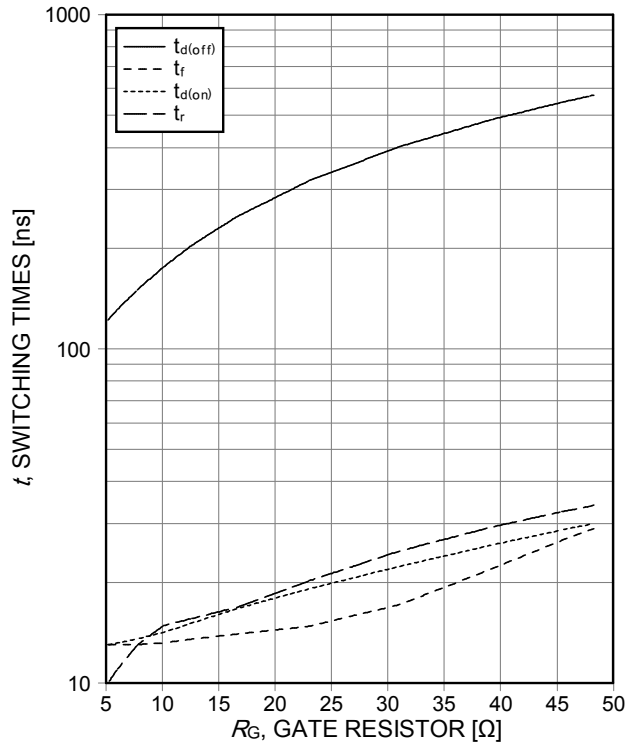


Figure 10. Typical switching times as a function of gate resistor
 (ind. load, $T_j=175^\circ\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $I_C=20\text{A}$, test circuit in Fig. E)

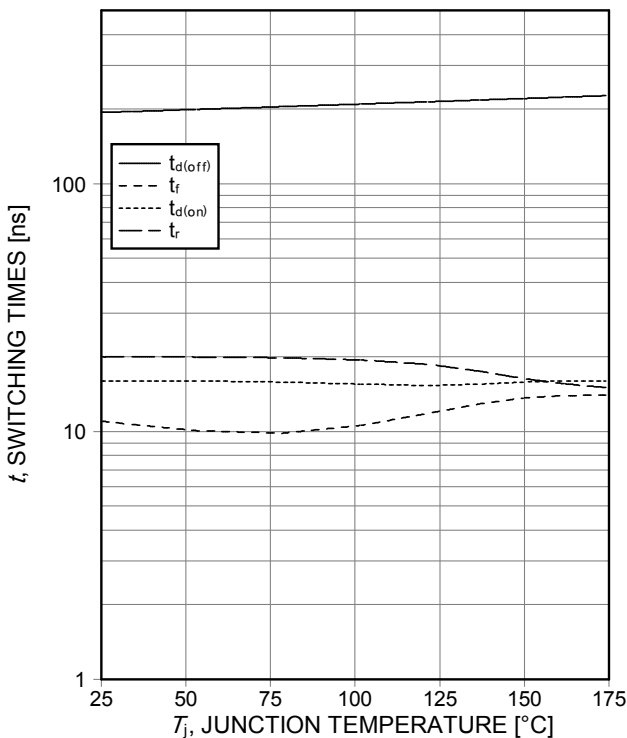


Figure 11. Typical switching times as a function of junction temperature
 (ind. load, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $I_C=20\text{A}$, $R_G=14,6\Omega$, test circuit in Fig. E)

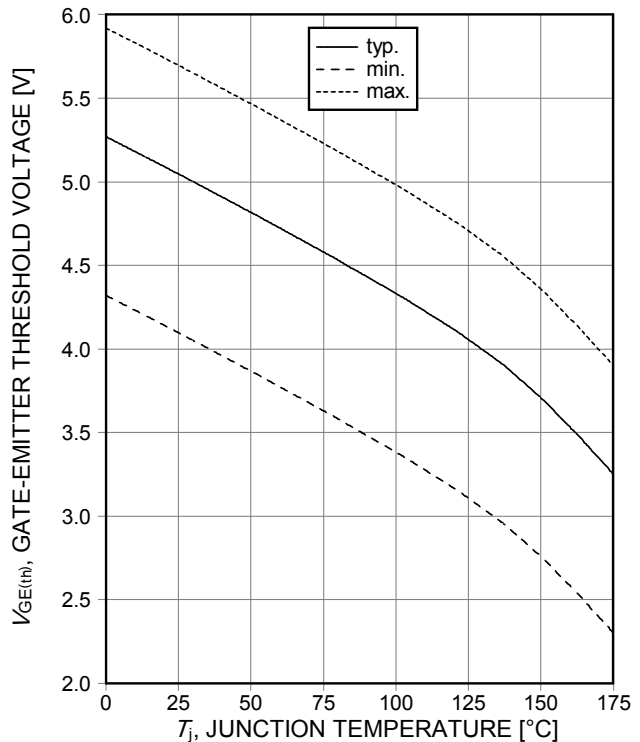


Figure 12. Gate-emitter threshold voltage as a function of junction temperature
 ($I_C=0.29\text{mA}$)

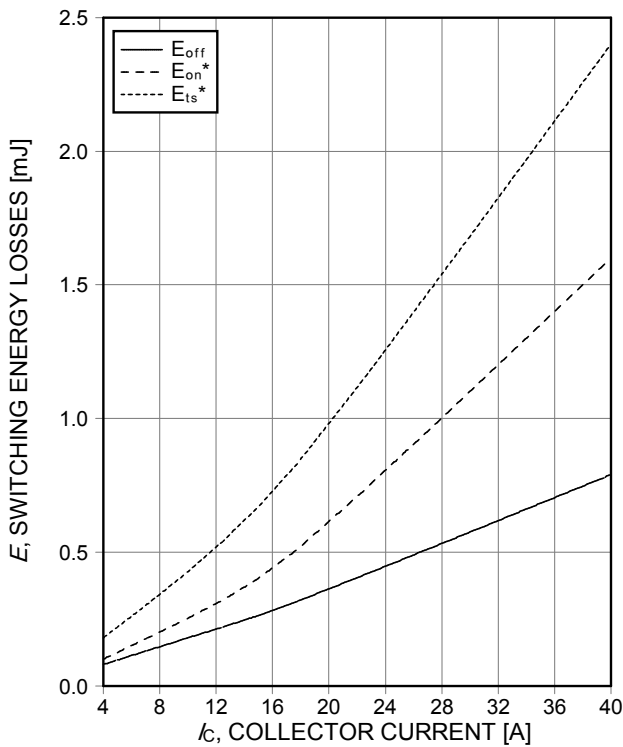


Figure 13. Typical switching energy losses as a function of collector current
 (ind. load, $T_j=175^\circ\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $R_G=14,6\Omega$, test circuit in Fig. E)

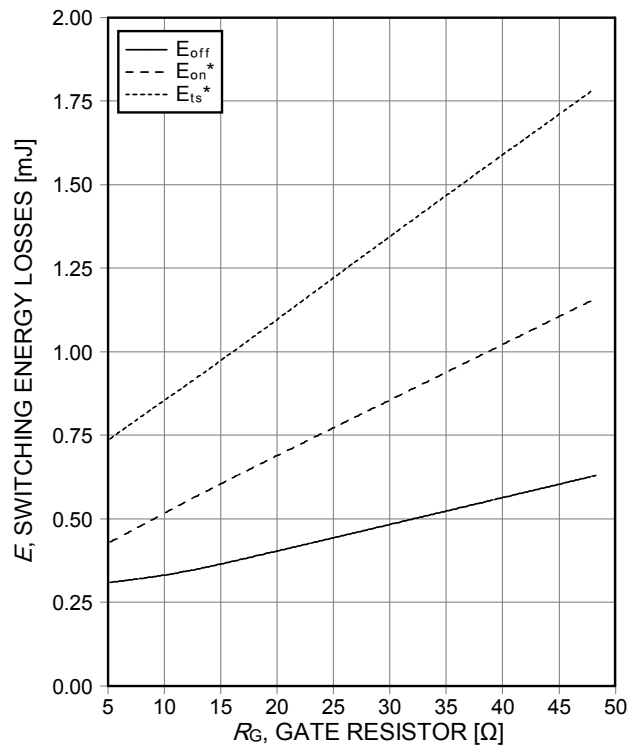


Figure 14. Typical switching energy losses as a function of gate resistor
 (ind. load, $T_j=175^\circ\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $I_c=20\text{A}$, test circuit in Fig. E)

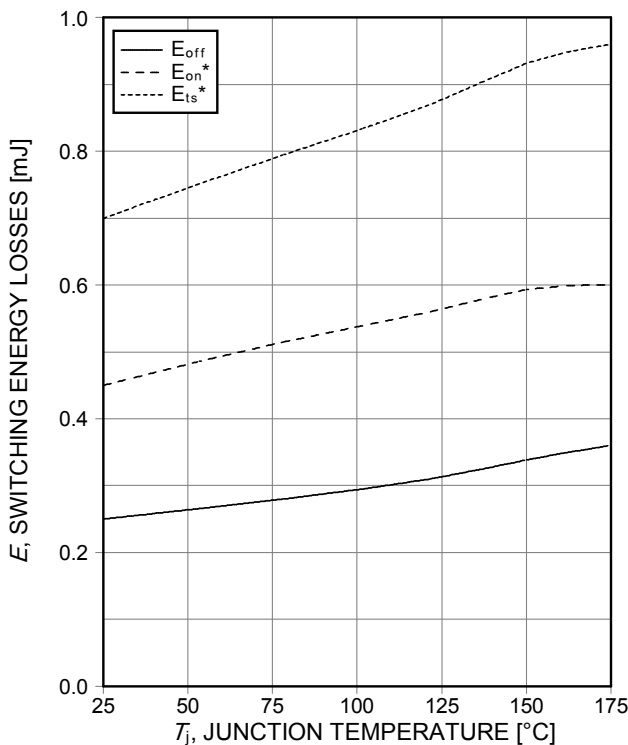


Figure 15. Typical switching energy losses as a function of junction temperature
 (ind load, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $I_c=20\text{A}$, $R_G=14,6\Omega$, test circuit in Fig. E)

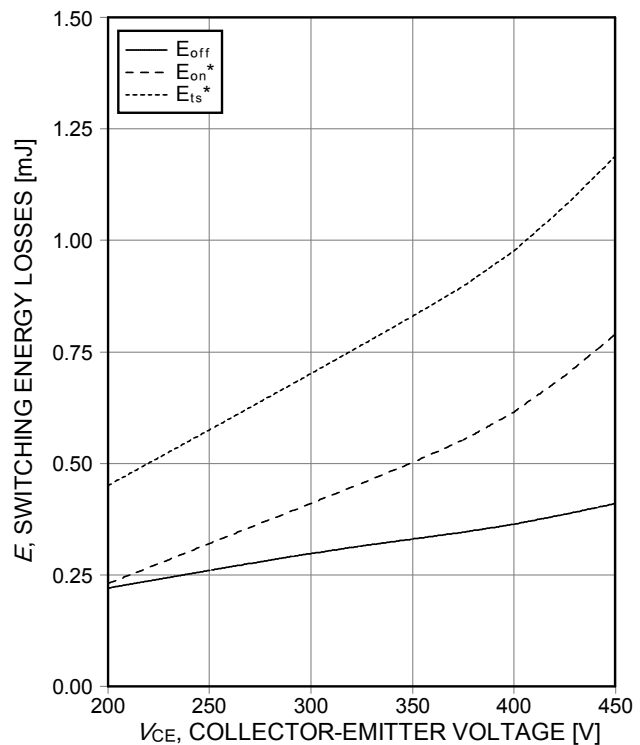


Figure 16. Typical switching energy losses as a function of collector emitter voltage
 (ind. load, $T_j=175^\circ\text{C}$, $V_{GE}=15/0\text{V}$, $I_c=20\text{A}$, $R_G=14,6\Omega$, test circuit in Fig. E)

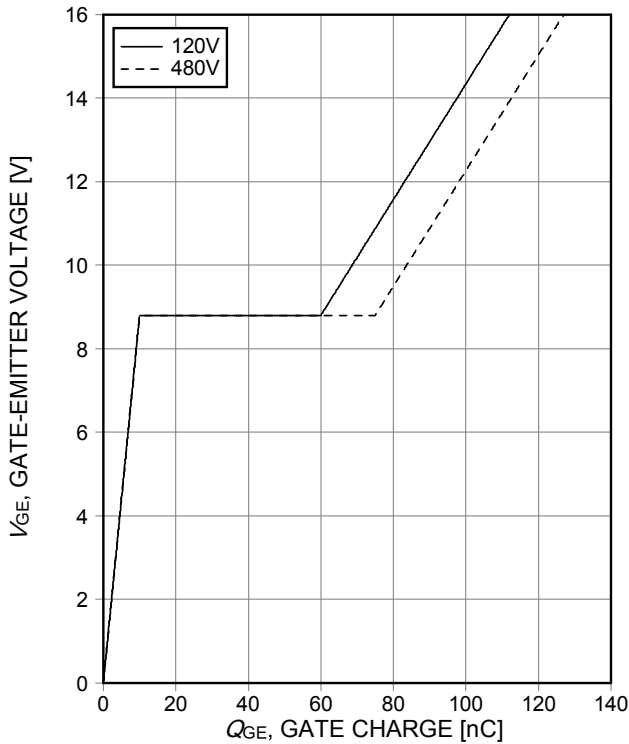


Figure 17. Typical gate charge
($I_C=20A$)

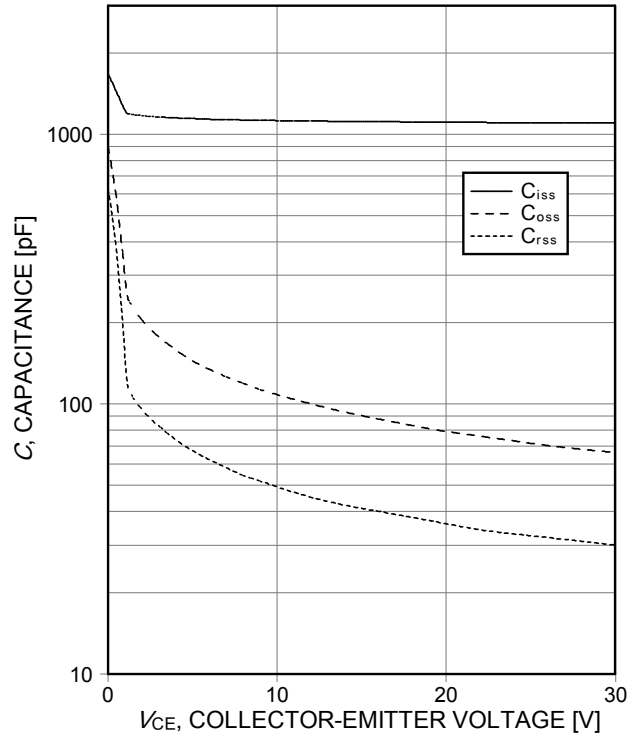


Figure 18. Typical capacitance as a function of collector-emitter voltage
($V_{GE}=0V$, $f=1MHz$)

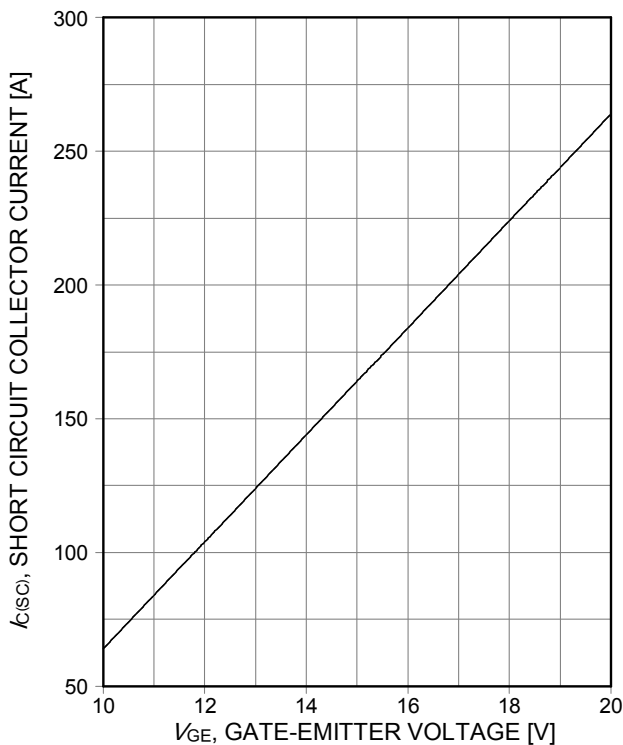


Figure 19. Typical short circuit collector current as a function of gate-emitter voltage
($V_{CE}\leq 400V$, start at $T_j=25^\circ C$)

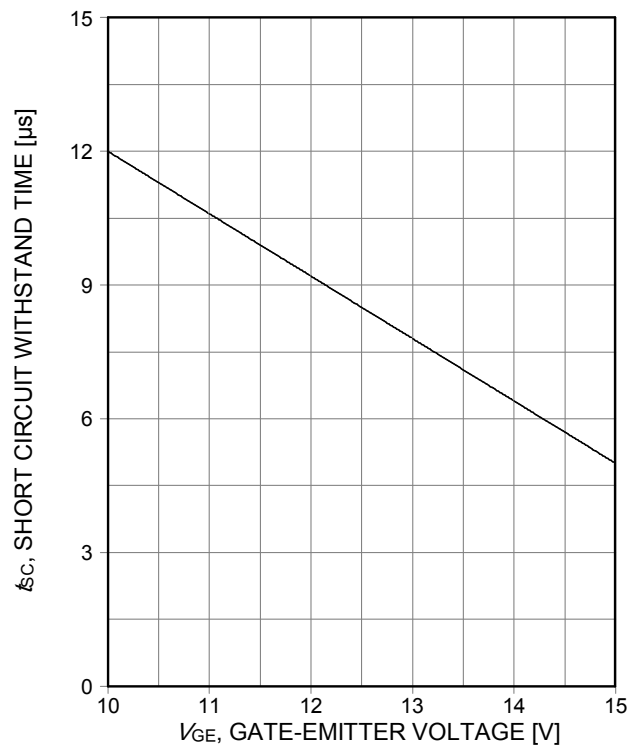


Figure 20. Short circuit withstand time as a function of gate-emitter voltage
($V_{CE}\leq 400V$, start at $T_j\leq 150^\circ C$)

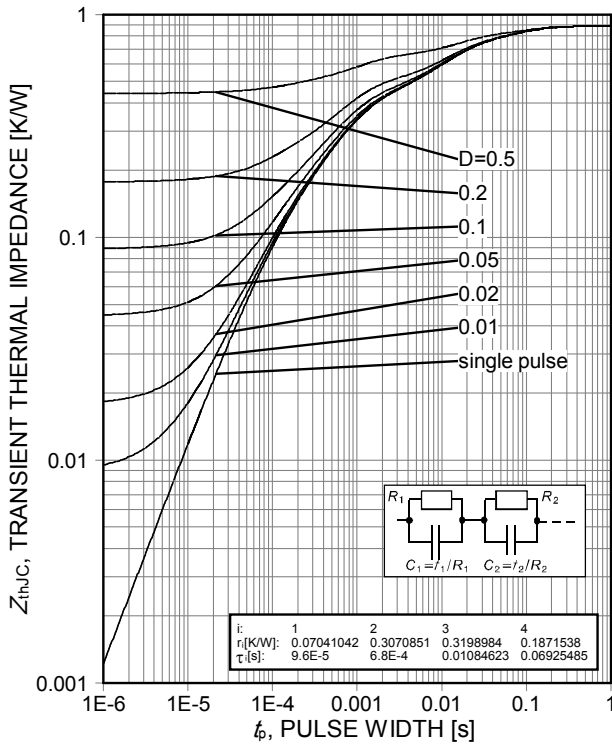


Figure 21. IGBT transient thermal impedance ($D = t_p/T$)

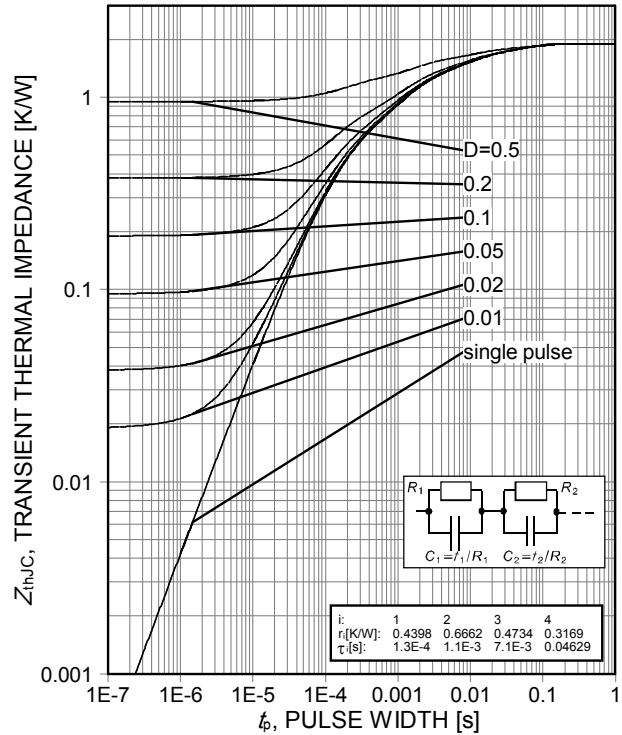


Figure 22. Diode transient thermal impedance as a function of pulse width ($D = t_p/T$)

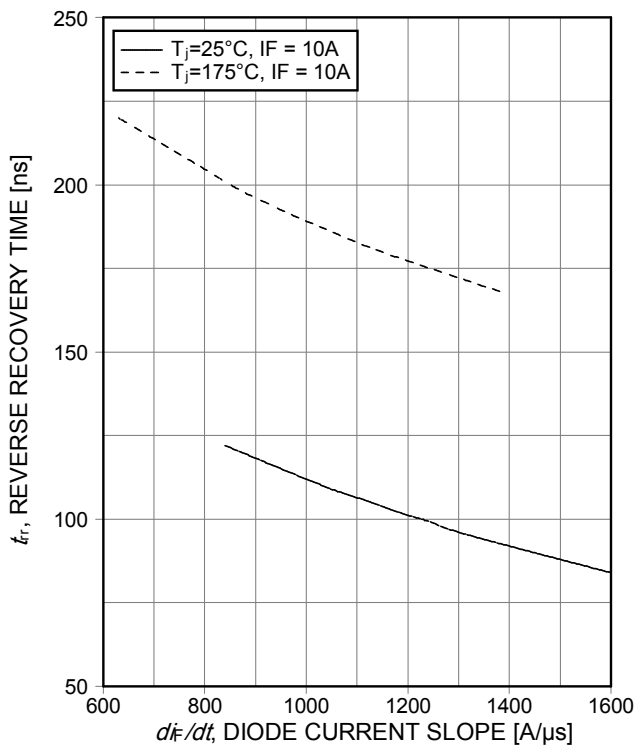


Figure 23. Typical reverse recovery time as a function of diode current slope ($V_R = 400V$)

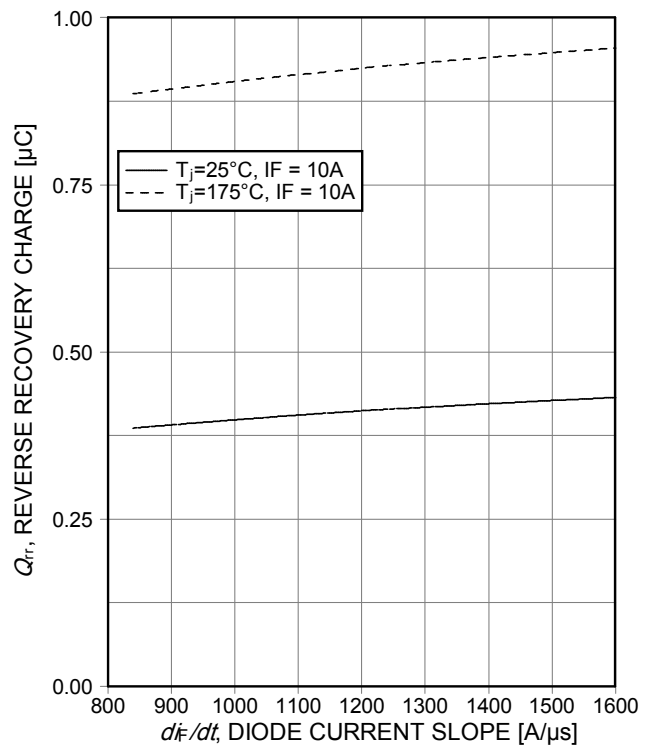


Figure 24. Typical reverse recovery charge as a function of diode current slope ($V_R = 400V$)

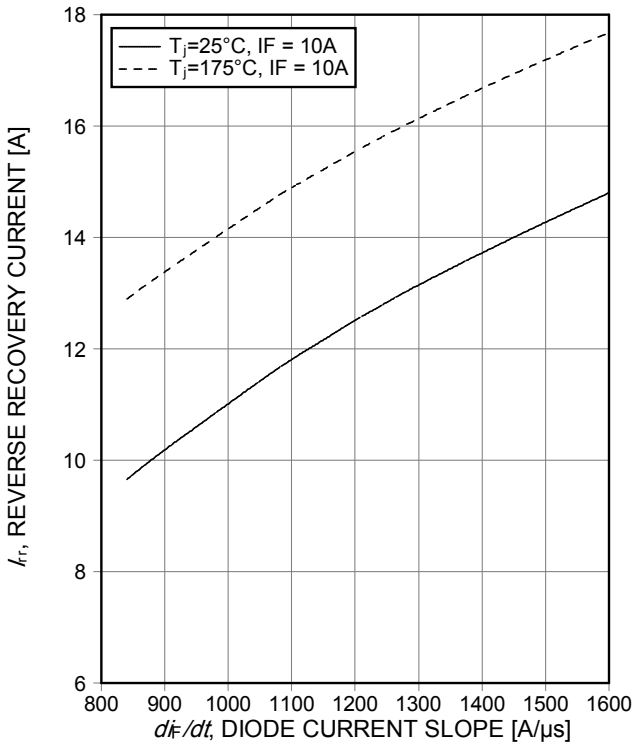


Figure 25. Typical reverse recovery current as a function of diode current slope ($V_R=400V$)

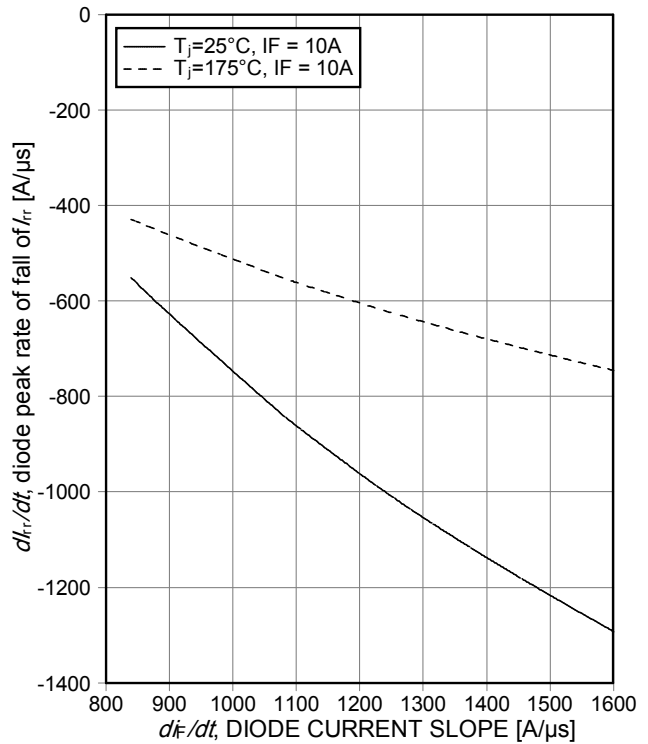


Figure 26. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope ($V_R=400V$)

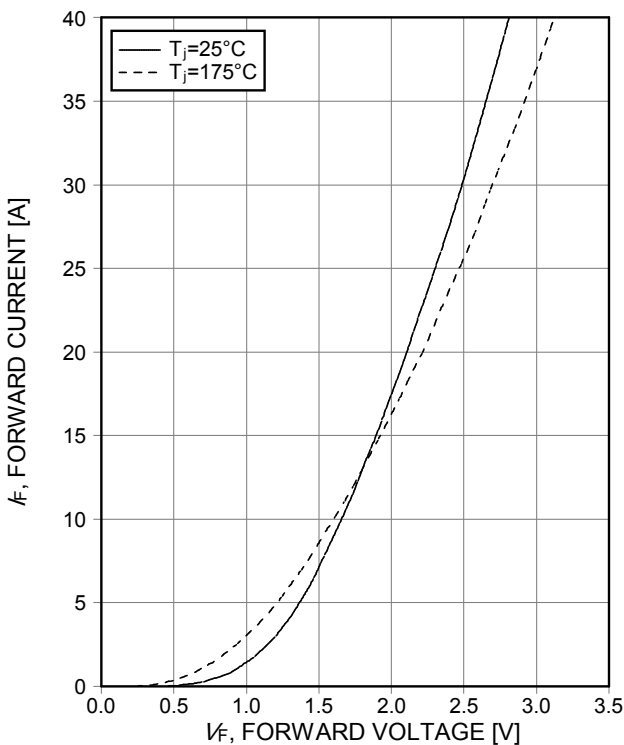


Figure 27. Typical diode forward current as a function of forward voltage

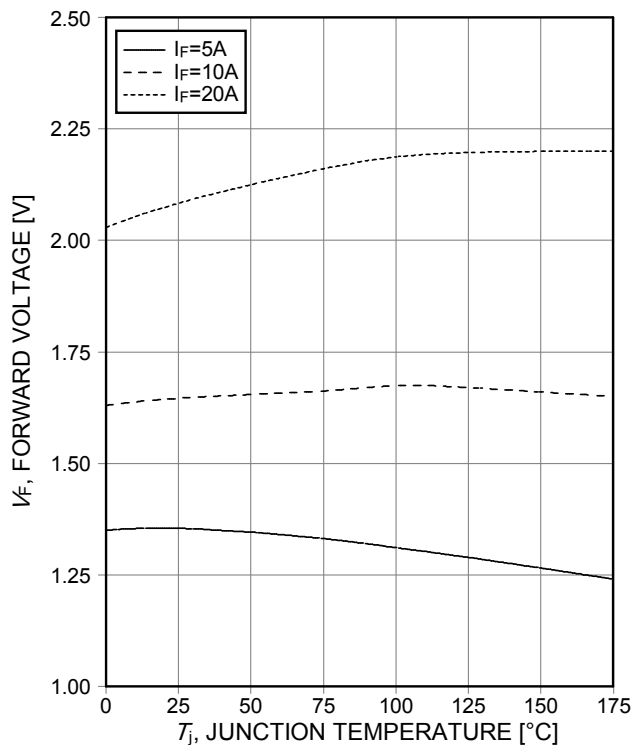
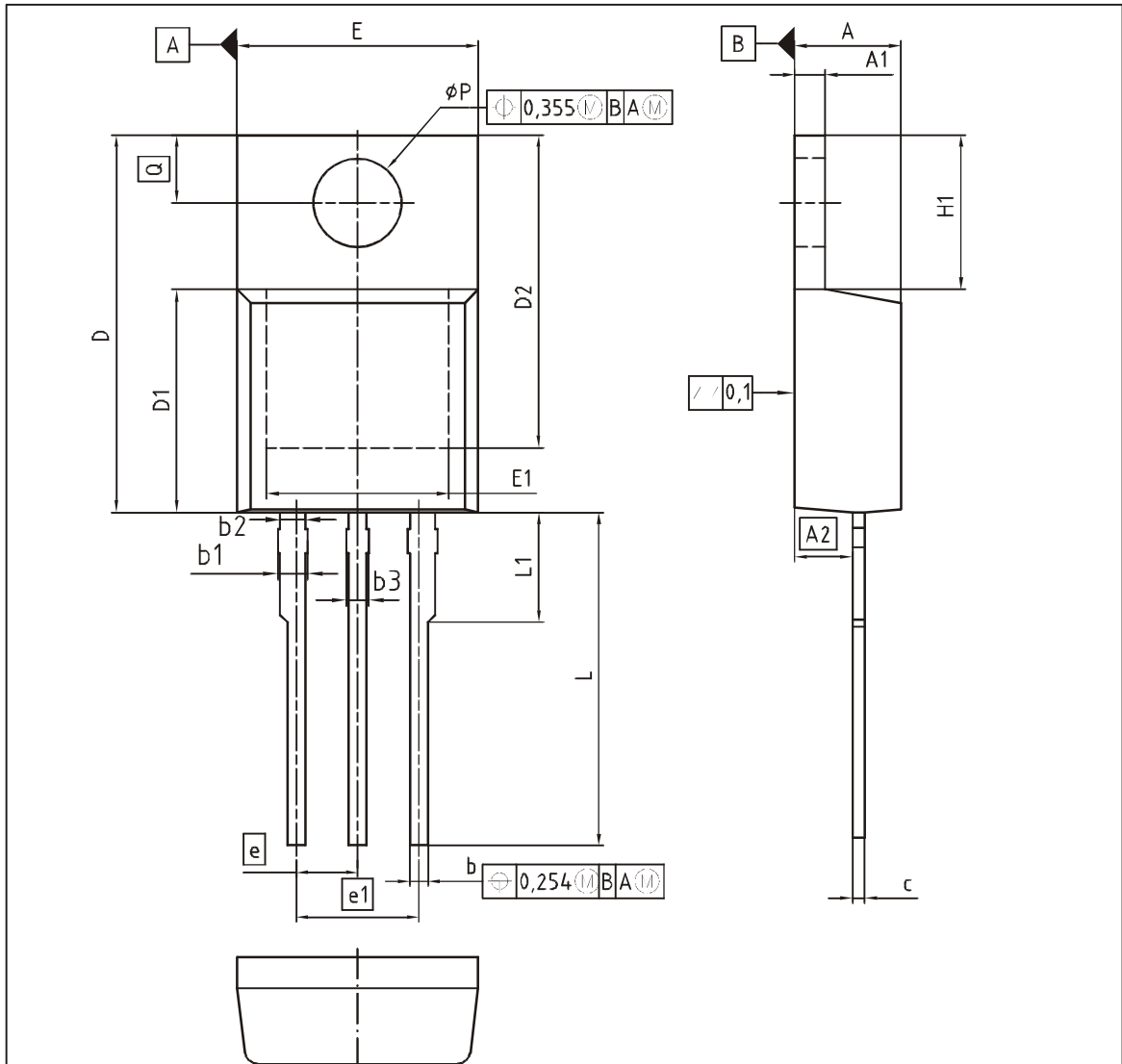


Figure 28. Typical diode forward voltage as a function of junction temperature

TO220-3-1 CONV.&LPL / TO220-3-21



| DIM | MILLIMETERS | | INCHES | |
|----------|-------------|-------|--------|-------|
| | MIN | MAX | MIN | MAX |
| A | 4.30 | 4.57 | 0.169 | 0.180 |
| A1 | 1.17 | 1.40 | 0.046 | 0.055 |
| A2 | 2.15 | 2.72 | 0.085 | 0.107 |
| b | 0.65 | 0.86 | 0.026 | 0.034 |
| b1 | 0.95 | 1.40 | 0.037 | 0.055 |
| b2 | 0.95 | 1.15 | 0.037 | 0.045 |
| b3 | 0.65 | 1.15 | 0.026 | 0.045 |
| c | 0.33 | 0.60 | 0.013 | 0.024 |
| D | 14.81 | 15.95 | 0.583 | 0.628 |
| D1 | 8.51 | 9.45 | 0.335 | 0.372 |
| D2 | 12.19 | 13.10 | 0.480 | 0.516 |
| E | 9.70 | 10.36 | 0.382 | 0.408 |
| E1 | 6.50 | 8.60 | 0.256 | 0.339 |
| e | 2.54 | | 0.100 | |
| e1 | 5.08 | | 0.200 | |
| N | 3 | | 3 | |
| H1 | 5.90 | 6.90 | 0.232 | 0.272 |
| L | 13.00 | 14.00 | 0.512 | 0.551 |
| L1 | - | 4.80 | - | 0.189 |
| ϕP | 3.60 | 3.89 | 0.142 | 0.153 |
| Q | 2.60 | 3.00 | 0.102 | 0.118 |

DOCUMENT NO.
Z8B00003318

SCALE

EUROPEAN PROJECTION

ISSUE DATE
23-08-2007

REVISION
05

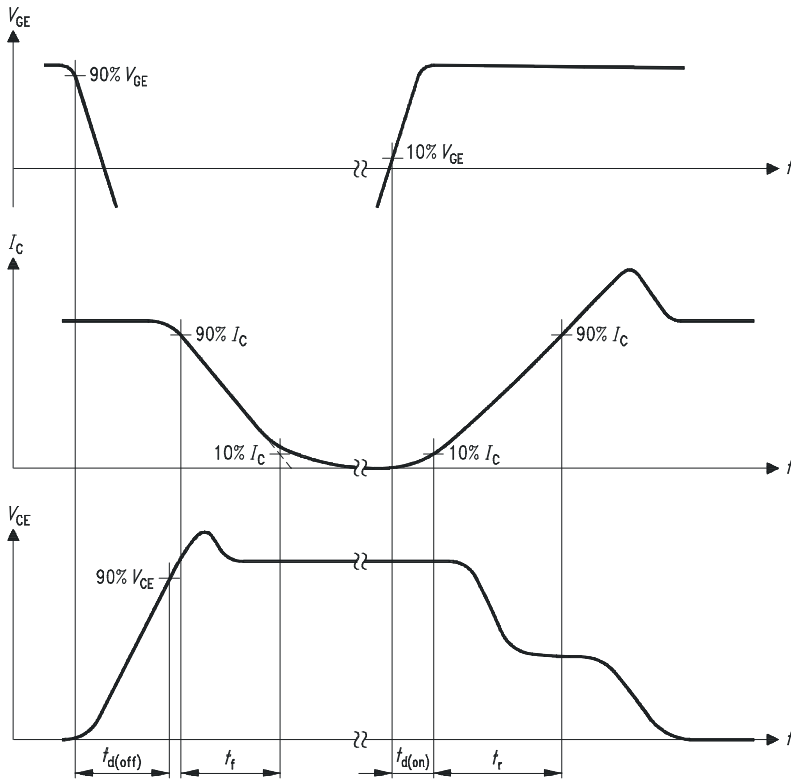


Figure A. Definition of switching times

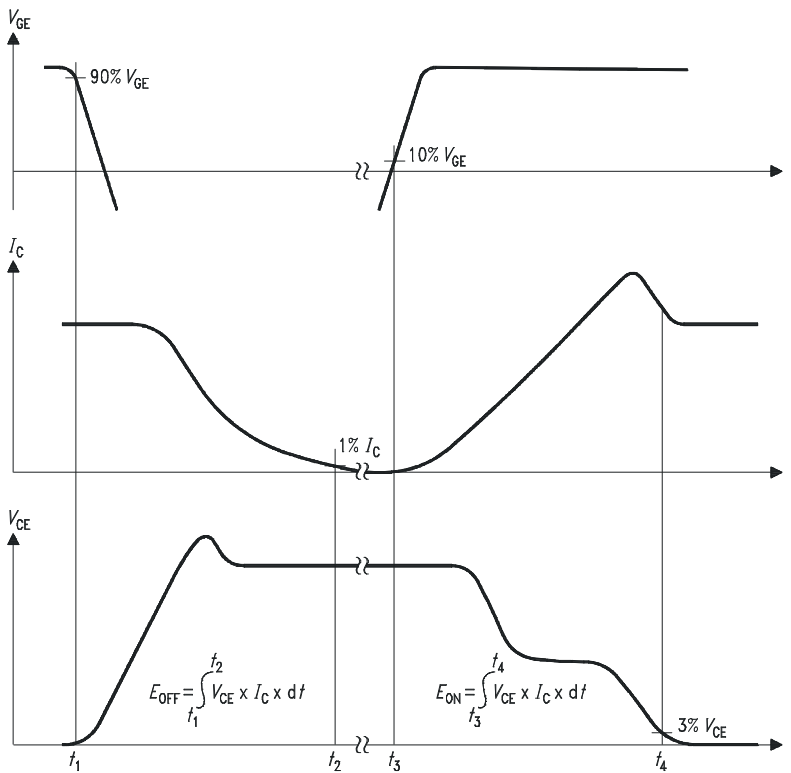


Figure B. Definition of switching losses

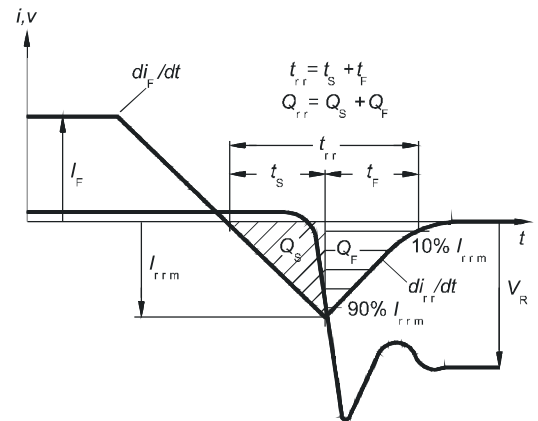


Figure C. Definition of diodes switching characteristics

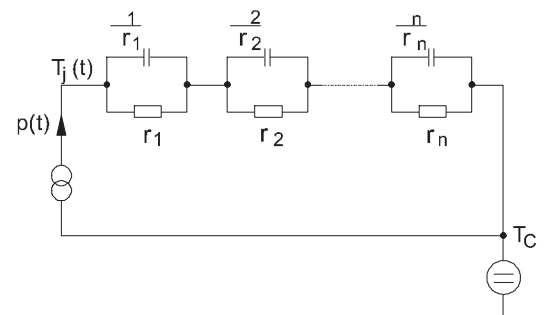


Figure D. Thermal equivalent circuit

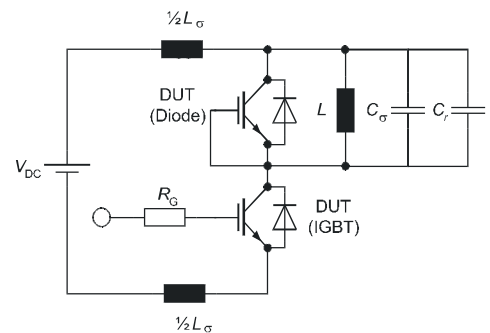


Figure E. Dynamic test circuit
Parasitic inductance L_{σ} ,
Parasitic capacitor C_{σ} ,
Relief capacitor C_r
(only for ZVT switching)

**Revision History**

IKP20N60H3

Revision: 2010-07-26, Rev. 1.1

Previous Revision

| Revision | Date | Subjects (major changes since last revision) |
|----------|------|--|
| 1.1 | - | Preliminary datasheet |

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Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

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- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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